

SANYO	No.2016A	2SD1627
		NPN Epitaxial Planar Silicon Transistor

Driver Applications

Applications

- . Motor drivers, hammer drivers, relay drivers, voltage regulator control

Features

- . High DC current gain ($h_{FE} \geq 4000$)
- . Wide ASO
- . Very small size making it easy to provide high-density, small-sized hybrid ICs.

Absolute Maximum Ratings at Ta=25°C

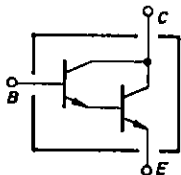
			unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	10	V
Collector Current	I_C	2	A
Collector Current(Pulse)	I_{CP}	3	A
Collector Dissipation	P_C	500	mW
	Mounted on ceramic board (250mm ² x 0.8mm)	1.5	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

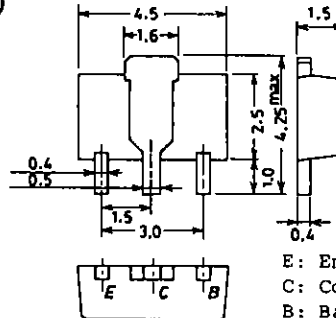
			min	typ	max	
Collector Cutoff Current	I_{CBO} $V_{CB}=20V, I_E=0$				1	μA
Emitter Cutoff Current	I_{EBO} $V_{EB}=8V, I_C=0$				1	μA
DC Current Gain	$h_{FE}(1)$ $V_{CE}=2V, I_C=500mA$	4000				
	$h_{FE}(2)$ $V_{CE}=2V, I_C=10mA$	3000				
Gain-Bandwidth Product	f_T $V_{CE}=10V, I_C=50mA$			120		MHz
C-E Saturation Voltage	$V_{CE(sat)}$ $I_C=600mA, I_B=0.15mA$			0.9	1.5	V
B-E Saturation Voltage	$V_{BE(sat)}$ $I_C=600mA, I_B=0.15mA$				2.0	V
C-B Breakdown Voltage	$V_{(BR)EBO}$ $I_C=10\mu A, I_E=0$	30				V
C-E Breakdown Voltage	$V_{(BR)CEO}$ $I_C=1mA, R_{BE}=\infty$	25				V
E-B Breakdown Voltage	$V_{(BR)EBO}$ $I_E=10\mu A, I_C=0$	10				V

Marking :DJ

Electrical Connection

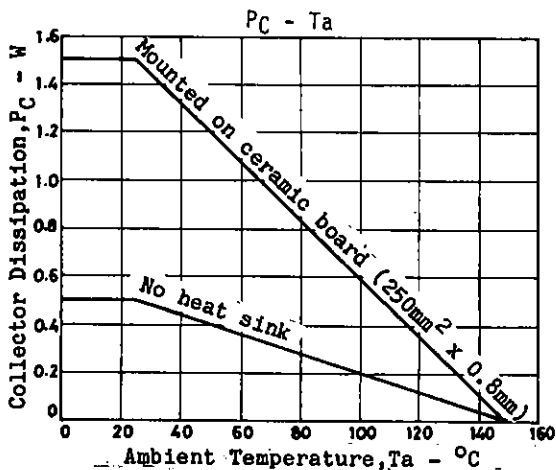
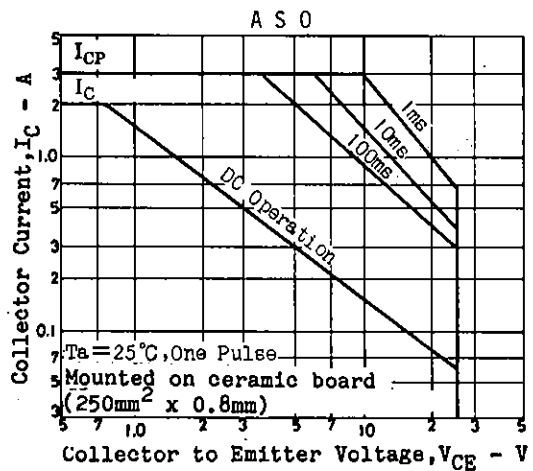
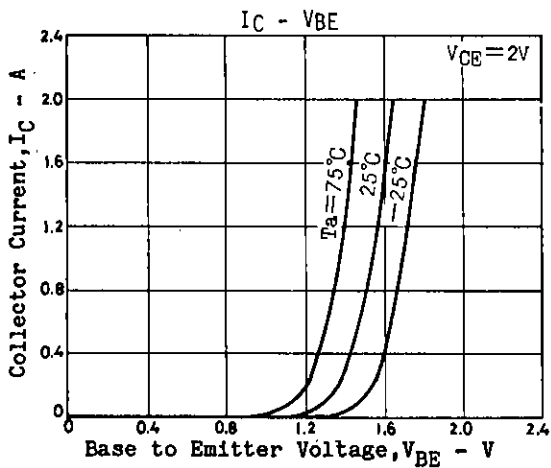
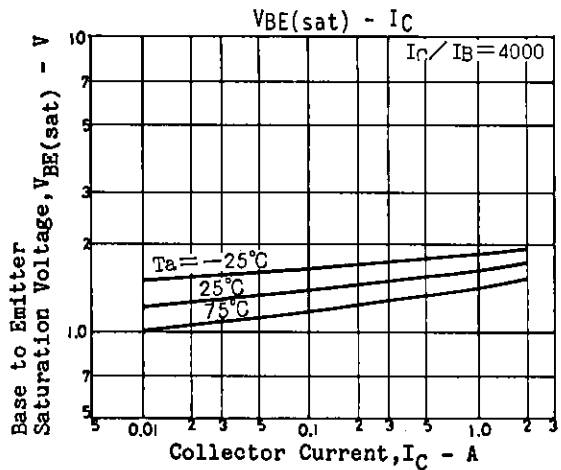
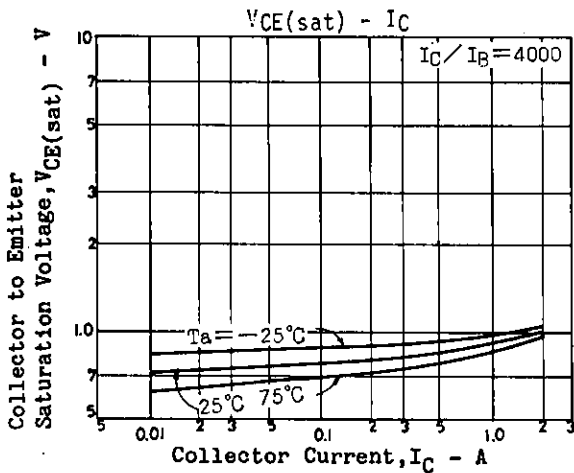
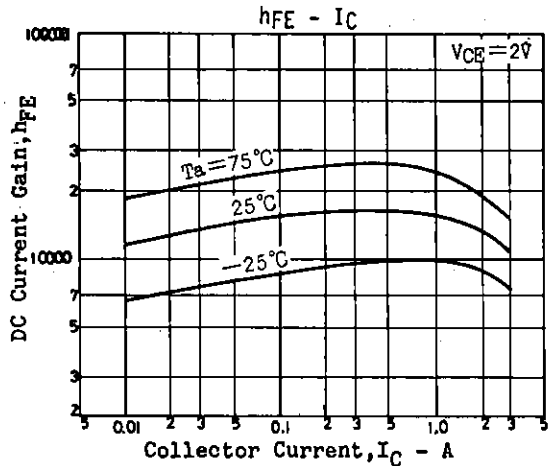
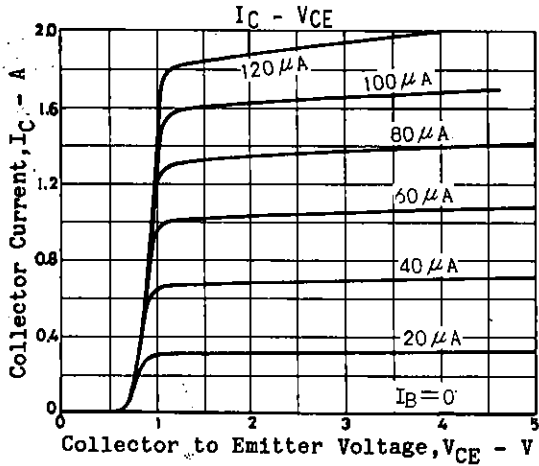


Package Dimensions 2038
(unit:mm)



E: Emitter
C: Collector
B: Base

SANYO: PCP
(Bottom View)



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